

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Mahendra K. Sunkara et al.

Filed: September 16, 2003

Serial No: 10/664,072

For: DIRECT SYNTHESIS OF OXIDE  
NANOSTRUCTURES OF LOW-MELTING METALS)

Atty. Docket No.: AD138/2001

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) Examiner: Luk, Emmanuel S.  
) Group Art Unit: 1722  
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**INFORMATION DISCLOSURE DOCUMENT**

Enclosed is a list and copies of references considered by Applicant to be pertinent in the  
examination of the above-identified patent application.

Applicant submits this Information Disclosure Statement in accordance with the duty of  
disclosure under 37CFR §1.56 and 1.97-1.98. This Statement is filed in accordance with 37 CFR  
§1.97(b)(4), prior to issuance of a First Office after the filing of a request for continued examination  
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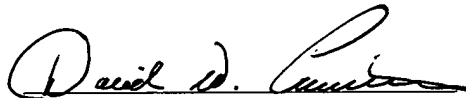
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Applicants(s) submitted herewith patents, publications or other information of which they are aware, which they believe may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR 1.56.

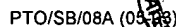
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Respectfully submitted,

A handwritten signature in black ink, appearing to read "David W. Carrithers", written over a horizontal line.

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**Complete if Known**

Application Number	10/664,072
Filing Date	September 16, 2003
First Named Inventor	Mahendra Kumar Sunkara
Art Unit	1722
Examiner Name	Emmanuel S. Luk
Attorney Docket Number	AD138/2001

Sheet	1	of
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## U.S. PATENT DOCUMENTS

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[illegible]

**OTHER PRIOR ART (Including Author, Title, Date Pertinent Pages, ETC.)**

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Examiner Signature		Date Considered	
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